



# **PRODUCT DATA SHEET**



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Datasheet

es Samples

Please note: Please check the JINGAO Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.jg-semi.cn. Please email any questions regarding the system integration to JINGAO\_questions@jgsemi.com.





N-Ch 20V Fast Switching MOSFETs

### **Product Summary**

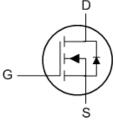
BVDSS	RDSON	ID		
20V	21mΩ	6.0A		



SOT23

- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent Cdv/dt effect decline
- ★ Advanced high cell density Trench technology





### **Absolute Maximum Ratings**

Symbol	Parameter	Rating	Units		
V <sub>DS</sub>	Drain-Source Voltage	20	V		
$V_{GS}$	Gate-Source Voltage	Drain-Source Voltage         20           Gate-Source Voltage         ±12           ntinuous Drain Current, V <sub>GS</sub> @ 4.5V¹         6.0           ntinuous Drain Current, V <sub>GS</sub> @ 4.5V¹         3.0           Pulsed Drain Current²         16.4           Total Power Dissipation³         1.0			
I <sub>D</sub> @T <sub>A</sub> =25°C	Continuous Drain Current, V <sub>GS</sub> @ 4.5V <sup>1</sup>	A			
ID@TA=70°C	Continuous Drain Current, V <sub>GS</sub> @ 4.5V <sup>1</sup> 3.0				
I <sub>DM</sub>	Pulsed Drain Current <sup>2</sup>				
P <sub>D</sub> @T <sub>A</sub> =25°C	Total Power Dissipation <sup>3</sup>	1.0	W		
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	°C		
TJ	Operating Junction Temperature Range	-55 to 150	°C		

#### **Thermal Data**

Symbol	Parameter	Тур.	Max.	Unit
Reja	Thermal Resistance Junction-ambient <sup>1</sup>		170	°C/W
R <sub>θJC</sub>	Thermal Resistance Junction-Case <sup>1</sup>			°C/W



## **Electrical Characteristics** (T<sub>J</sub>=25 °C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units	
Off Charac	teristic		'		•		
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250µA	20	-	_	V	
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V,	-	-	1.0	μA	
I <sub>GSS</sub>	Gate to Body Leakage Current	V <sub>DS</sub> =0V, V <sub>GS</sub> =±12V	-	-	±100	nA	
On Charac	teristics		·				
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$ , $I_{D}=250\mu A$	0.4	0.7	1	V	
	Static Drain-Source on-Resistance	V <sub>GS</sub> =4.5V, I <sub>D</sub> =4A	-	21	27	mΩ	
$R_{DS(on)}$	note2	V <sub>GS</sub> =2.5V, I <sub>D</sub> =3A	-	29	44		
Dynamic C	Characteristics		'				
C <sub>iss</sub>	Input Capacitance	1/ /01/1/ 01/	-	358	-	pF	
Coss	Output Capacitance	V <sub>DS</sub> =10V, V <sub>GS</sub> =0V, f=1.0MHz V <sub>DS</sub> =10V, I <sub>D</sub> =2A,	-	69.3	-	pF	
C <sub>rss</sub>	Reverse Transfer Capacitance		-	58.5	-	pF	
Qg	Total Gate Charge	\/ -40\/ I -24	-	5.6	-	nC	
Q <sub>gs</sub>	Gate-Source Charge	' '	-	0.8	-	nC	
$Q_{gd}$	Gate-Drain("Miller") Charge	V <sub>GS</sub> -4.5V	-	1	-	nC	
Switching	Characteristics		·				
t <sub>d(on)</sub>	Turn-on Delay Time	101	-	5	-	ns	
t <sub>r</sub>	Turn-on Rise Time	V <sub>DS</sub> =10V, V <sub>GS</sub> =0V, f=1.0MHz V <sub>DS</sub> =10V, I <sub>D</sub> =2A, V <sub>GS</sub> =4.5V V <sub>DS</sub> =10V, I <sub>D</sub> =4A, R <sub>GEN</sub> =3Ω, V <sub>GS</sub> =4.5V	-	30	-	ns	
t <sub>d(off)</sub>	Turn-off Delay Time	, -	-	48	-	ns	
t <sub>f</sub>	Turn-off Fall Time	V <sub>GS</sub> -4.5V	-	36	-	ns	
Drain-Sou	rce Diode Characteristics and Maxim	um Ratings	·				
Is	Maximum Continuous Drain to Source Diode Forward Current		-	-	4	Α	
I <sub>SM</sub>	Maximum Pulsed Drain to Source Dic	-	-	16	Α		
$V_{\text{SD}}$	Drain to Source Diode Forward Voltage	V <sub>GS</sub> =0V, I <sub>S</sub> =4A	-	-	1.2	V	

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width≤300µs, Duty Cycle≤0.5%



## **Typical Performance Characteristics**

Figure1: Output Characteristics

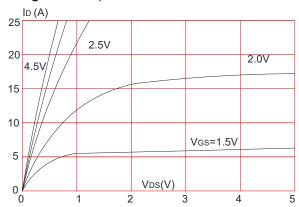


Figure 3:On-resistance vs. Drain Current

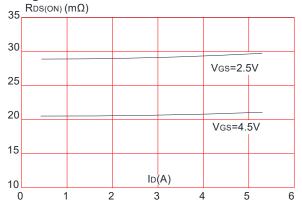


Figure 5: Gate Charge Characteristics

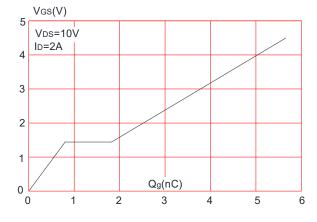


Figure 2: Typical Transfer Characteristics

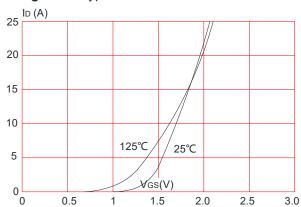


Figure 4: Body Diode Characteristics

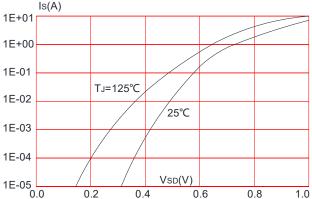
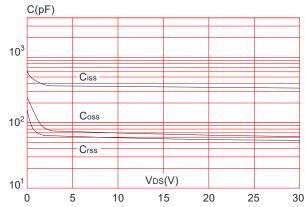


Figure 6: Capacitance Characteristics



**Figure 7:** Normalized Breakdown Voltage vs. Junction Temperature

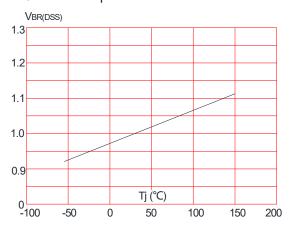
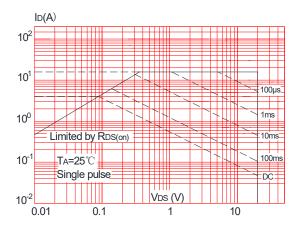
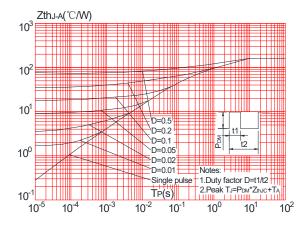


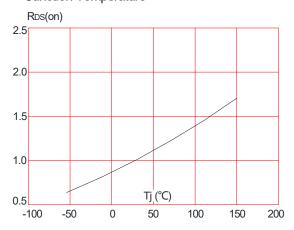
Figure 9: Maximum Safe Operating Area



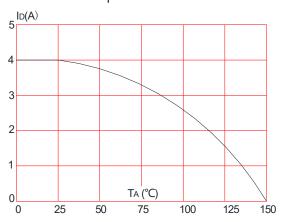
**Figure.11:** Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



**Figure 8:** Normalized on Resistance vs. Junction Temperature

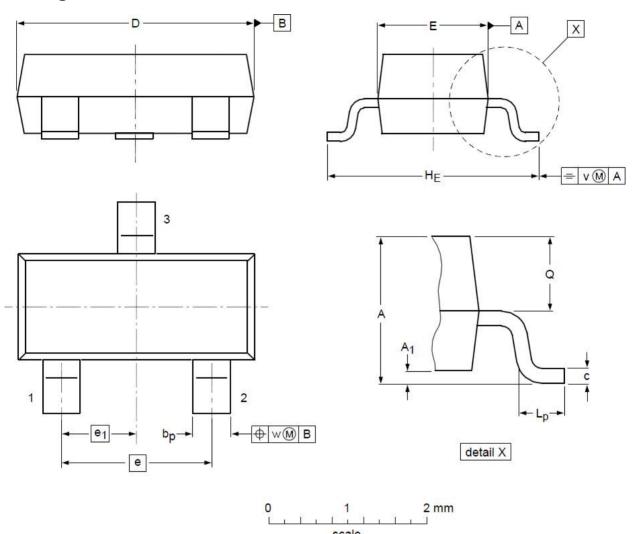


**Figure 10:** Maximum Continuous Drain Current vs. Ambient Temperature





## Package Mechanical Data-SOT-23



#### **DIMENSIONS** ( unit : mm )

Symbol	Min	Тур	Max	Symbol	Min	Тур	Max
Α	0.90	1.01	1.15	<b>A</b> <sub>1</sub>	0.01	0.05	0.10
b <sub>p</sub>	0.30	0.42	0.50	С	0.08	0.13	0.15
D	2.80	2.92	3.00	E	1.20	1.33	1.40
е		1.90		<b>e</b> <sub>1</sub>		0.95	
HE	2.25	2.40	2.55	Lp	0.30	0.42	0.50
Q	0.45	0.49	0.55	v		0.20	
w		0.10					



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